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Karen Cinq-Mars 3/15/04
(Signature & date)



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of _____ : March 15, 2004
Gregory Freeman, et al. _____ : Group Art Unit: to be assigned
Serial No. 10/708,563 _____ : Examiner: to be assigned
Filed: 3/11/04 _____ : International Business Machines Corporation
2070 Route 52
Hopewell Junction, NY 12533

TITLE: STRUCTURE AND METHOD OF FORMING A BIPOLAR TRANSISTOR HAVING A VOID
BETWEEN EMITTER AND EXTRINSIC BASE

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the non-US patents and publications as listed on Form PTO-1449, attached hereto.

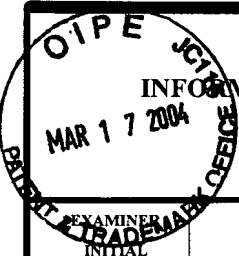
In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,
Gregory Freeman, et al.

By H. Daniel Schnurmann

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**INFORMATION DISCLOSURE CITATION***(Use several sheets if necessary)*

Docket Number (Optional)

FIS920030255US1

Application Number

10/708,563

Applicant(s)

Daniel C. Edelstein, et al.

Filing Date

1/6/04

Group Art Unit

Not Yet Assigned**OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, Etc.)*

Jagannathan, et al., "Self-aligned SiGe NPN Transistors with 285 GHz f_{MAX} and 207 GHz f_T in a Manufacturable Technology". IEEE Electron Device letters 23, 259 (2002)

J.S. Rieh, et al., "SiGe HBTs with Cut-off Frequency of 350 GHz", International Electron Device Meeting Technical Digest, 771 (2002)

M.W. Xu et al. "Ultra Low Power SiGe:C HBT for 0.18 um RF-FiCMOS, " Proceedings of the IEEE International Electron Devices Meeting, 2003.

EXAMINER**DATE CONSIDERED**

***EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.